

MULTIPLE WIDTH AND/OR THICKNESS WRITE LINE IN MRAM

ABSTRACT

[0047] A magnetic random access memory (MRAM) cell including an MRAM cell stack located over a substrate and first and second write lines spanning opposing termini of the MRAM cell stack. At least one of the first and second write lines includes at least one first portion spanning the MRAM cell stack and at least one second portion proximate the MRAM cell stack. The first and second portions have first and second cross-sectional areas, respectively, wherein the first cross-sectional area is substantially less than the second cross-sectional area.